

# MBR40150FCT -MBR40200FCT

### 40A HIGH VOLTAGE DUAL SCHOTTKY BARRIER RECTIFIER

### **Features**

- Power Schottky Barrier Chip
- Guard Ring for Transient Protection
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Current Capability
- Epoxy Meets UL 94V-0 Classification
- Ideally Suited for Use in High Frequency SMPS, Inverters and As Free Wheeling Diodes

# **Mechanical Data**

Case: ITO-220, Full Molded Plastic
Terminals: Plated Leads Solderable per

MIL-STD-202, Method 208 Polarity: See Diagram

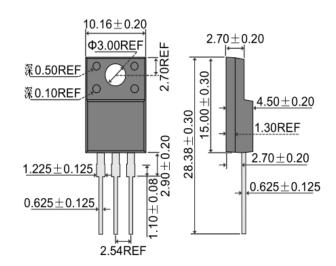
Weight: 1.9 grams (approx.)

Mounting Position: Any

Mounting Torque: 0.6 N.m Max.

Lead Free: For RoHS / Lead Free Version

# ITO-220AB





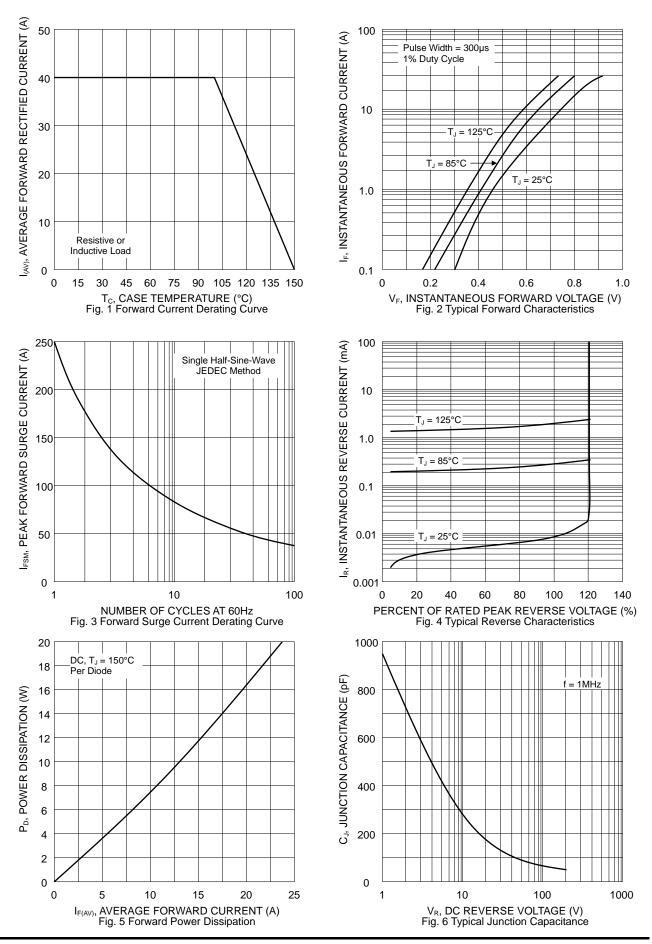
# Maximum Ratings and Electrical Characteristics @TA=25°C unless otherwise specified

Single Phase, half wave, 60Hz, resistive or inductive load. For capacitive load, derate current by 20%.

| Characteristic  | Symbol             | MBR40150FCT  | MBR40200FCT | Unit |
|---|--------------------|--------------|-------------|------|
| Peak Repetitive Reverse Voltage<br>Working Peak Reverse Voltage<br>DC Blocking Voltage                                | VRRM<br>VRWM<br>VR | 150 200      |             | V    |
| RMS Reverse Voltage   | VR(RMS)            | 105          | 140         | V    |
| Average Rectified Output Current Total Device @T <sub>C</sub> = 100°C Per Diode                                       | lo                 | 40<br>20     |             | А    |
| Non-Repetitive Peak Forward Surge Current<br>8.3ms Single Half Sine-Wave Superimposed on<br>Rated Load (JEDEC Method) | IFSM               | 250          |             | А    |
| Forward Voltage per diode $@I_F = 20A, T_J = 25^{\circ}C$ $@I_F = 20A, T_J = 125^{\circ}C$                            | VFM                | 0.92<br>0.82 |             | V    |
| Peak Reverse Current $@T_J = 25^{\circ}C$<br>At Rated DC Blocking Voltage $@T_J = 100^{\circ}C$                       | IRM                | 0.5<br>10    |             | mA   |
| Typical Junction Capacitance (Note 1)   | Cı                 | 500          |             | pF   |
| Thermal Resistance Junction to Ambient per diode Thermal Resistance Junction to Case per diode                        | R JA<br>R JC       | 52<br>4.0    |             | °C/W |
| RMS Isolation Voltage Terminals to Case, t = 1 min  | Viso               | 1500         |             | V    |
| Operating and Storage Temperature Range   | ТJ, Tsтg           | -55 to +150  |             | °C   |

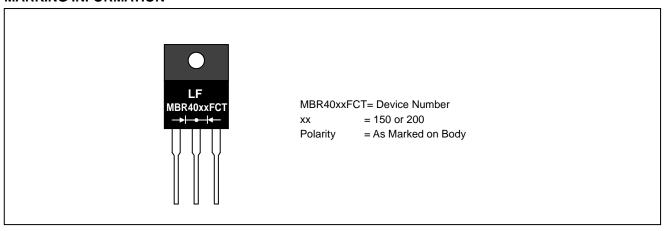
Note: 1. Measured at 1.0 MHz and applied reverse voltage of 4.0V D.C.

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### **MARKING INFORMATION**



# **PACKAGING INFORMATION**

#### **BULK**

| Tube Size      | Quantity | Inner Box Size | Quantity | Carton Size     | Quantity | Approx. Gross Weight (KG) |
|----------------|----------|----------------|----------|-----------------|----------|---------------------------|
| L x W x H (mm) | (PCS)    | L x W x H (mm) | (PCS)    | L x W x H (mm)  | (PCS)    |                           |
| 525 x 31 x 6   | 50       | 558 x 150 x 40 | 1,000    | 570 x 235 x 170 | 5,000    | 11.85                     |

### RECOMMENDED SCREW MOUNTING ARRANGEMENT

The full molded plastic package affords a major reduction of hardware as compared to a standard TO-220 package. However, precautions should be made in mounting procedure.

A conical washer should be used to apply proper force to the device. Screw should not be tightened with any type of air-forced torque or equipment that may cause crack on device package.

A layer of thermal grease or thermal pad in the interface will be considerably helpful for heat dissipation.

